



STx11NM60N

N-channel 600 V, 0.37 Ω , 10 A MDmesh™ II Power MOSFET
TO-220, TO-220FP, I²PAK, IPAK, DPAK, D²PAK

Features

Type	V _{DSS} (@T _J max)	R _{DS(on)} max	I _D
STB11NM60N-1	650 V	0.45 Ω	10 A
STB11NM60N	650 V	0.45 Ω	10 A
STD11NM60N	650 V	0.45 Ω	10 A
STD11NM60N-1	650 V	0.45 Ω	10 A
STF11NM60N	650 V	0.45 Ω	10 A ⁽¹⁾
STP11NM60N	650 V	0.45 Ω	10 A

1. Limited only by maximum temperature allowed

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Application

- Switching applications

Description

This series of devices is designed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

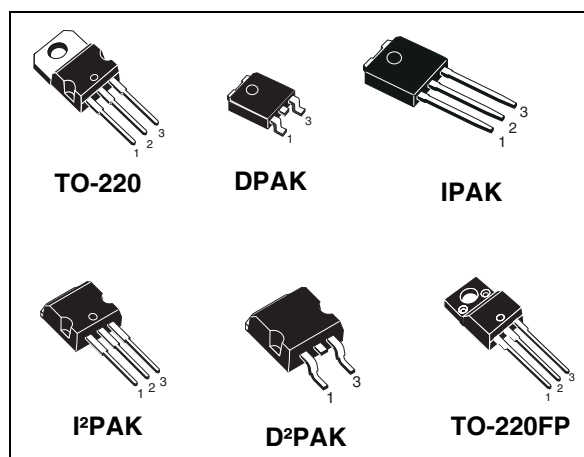


Figure 1. Internal schematic diagram

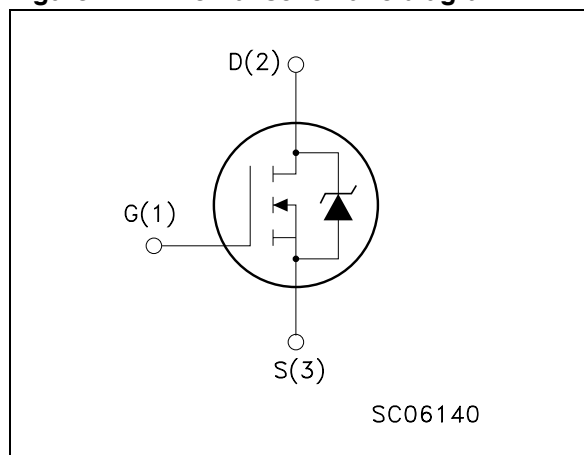


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB11NM60N-1	B11NM60N	I ² PAK	Tube
STB11NM60N	11NM60N	D ² PAK	Tape and reel
STD11NM60N-1	D11NM60N	IPAK	Tube
STD11NM60N	D11NM60N	DPAK	Tape and reel
STP11NM60N	P11NM60N	TO-220	Tube
STF11NM60N	F11NM60N	TO-220FP	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220,I ² PAK, D ² PAK,DPAK,IPAK	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} = 0)	600		V
V _{GS}	Gate-source voltage	± 25		V
I _D	Drain current (continuous) at T _C = 25 °C	10	10 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	6.3	6.3 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	40	40 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	90	25	W
	Derating factor	0.8	0.2	W/°C
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)		2500	V
T _{stg}	Storage temperature	-55 to 150		°C
T _J	Max. operating junction temperature	150		°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤ 10 A, di/dt ≤ 400 A/μs, V_{DD} = 80% V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	Value						Unit
		TO-220	I ² PAK	DPAK	D ² PAK	IPAK	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	1.38					5	°C/W
R _{thj-amb}	Thermal resistance junction-amb max	62.5				100	62.5	°C/W
R _{thj-pcb}	Thermal resistance junction-pcb max			50	30			°C/W
T _I	Maximum lead temperature for soldering purposes	300						°C

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _J max)	3.5	A
E _{AS}	Single pulse avalanche energy (starting T _J = 25 °C, I _D = I _{AS} , V _{DD} = 50 V)	200	mJ

2 Electrical characteristics

(T_{CASE}=25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0	600			V
dv/dt ⁽¹⁾	Drain-source voltage slope	V _{DD} = 400 V, I _D = 5 A, V _{GS} = 10 V	45			V/ns
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = Max rating, V _{DS} =Max rating, T _c =125 °C			1 10	μA μA
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ±20 V			±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 5 A		0.37	0.45	Ω

1. Characteristic value at turn off on inductive load

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} = 15 V, I _D = 5 A		7.5		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 50 V, f = 1 MHz, V _{GS} = 0		850 44 5		pF pF pF
C _{oss eq.} ⁽²⁾	Equivalent output capacitance	V _{GS} = 0, V _{DS} = 0 to 480 V		130		pF
R _g	Gate input resistance	f = 1 MHz Gate DC Bias = 0 Test signal level = 20 mV open drain		3.7		Ω
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V _{DD} = 480 V, I _D = 10 A V _{GS} = 10 V <i>Figure 19</i>		31 4.2 15.9		nC nC nC

1. Pulsed: pulse duration = 300 μs, duty cycle 1.5%

2. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 5\text{ A}$,		22		ns
t_r	Rise time	$R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$		18.5		ns
$t_{d(off)}$	Turn-off delay time	Figure 18		50		ns
t_f	Fall time	Figure 23		12		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				10	A
I_{SDM}	Source-drain current (pulsed)				40	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 10\text{ A}$, $V_{GS}=0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,		340		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100\text{ V}$		3.26		μC
I_{RRM}	Reverse recovery current	Figure 20		19.2		A
t_{rr}	Reverse recovery time	$V_{DD} = 100\text{ V}$		460		ns
Q_{rr}	Reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$, $I_{SD} = 10\text{ A}$		4.42		μC
I_{RRM}	Reverse recovery current	$T_J = 150\text{ }^\circ\text{C}$ Figure 20		19.2		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

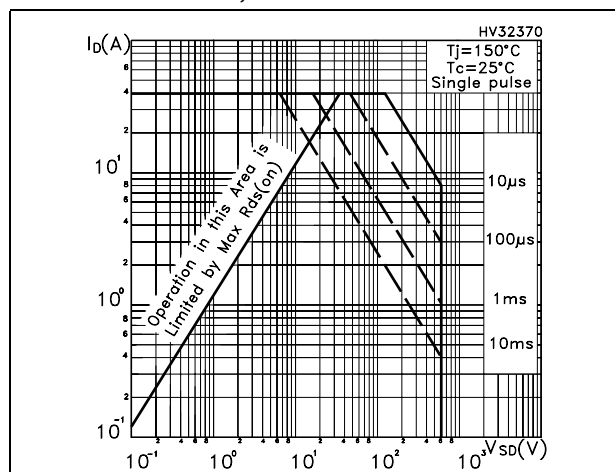
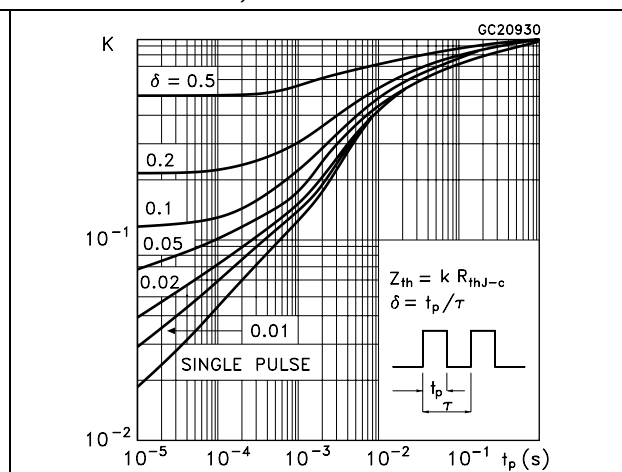
Figure 2. Safe operating area for TO-220, I²PAK, D²PAK**Figure 3. Thermal impedance for TO-220, I²PAK, D²PAK**

Figure 4. Safe operating area for TO-220FP

Figure 5. Thermal impedance for TO-220FP

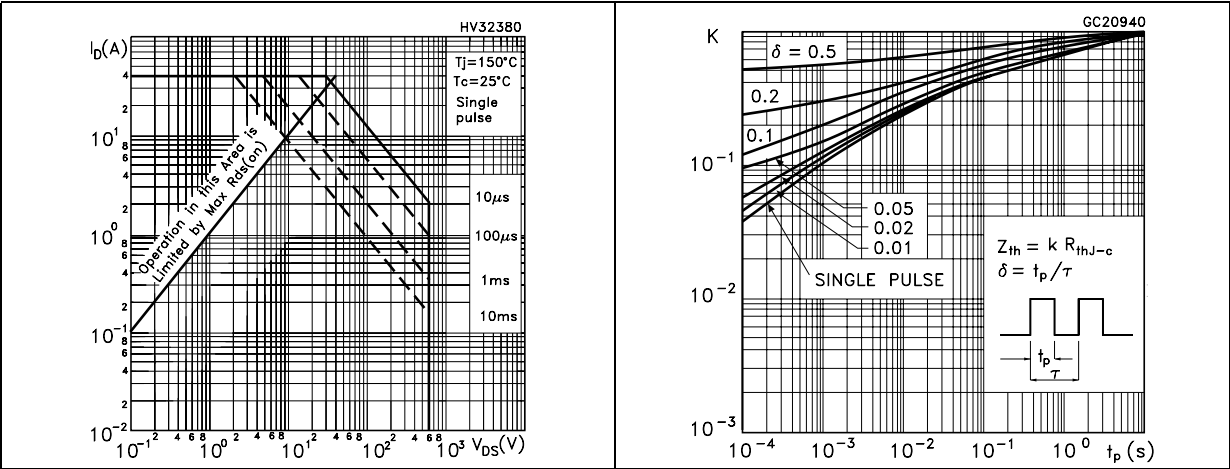


Figure 6. Safe operating area for DPAK, IPAK

Figure 7. Thermal impedance for DPAK, IPAK

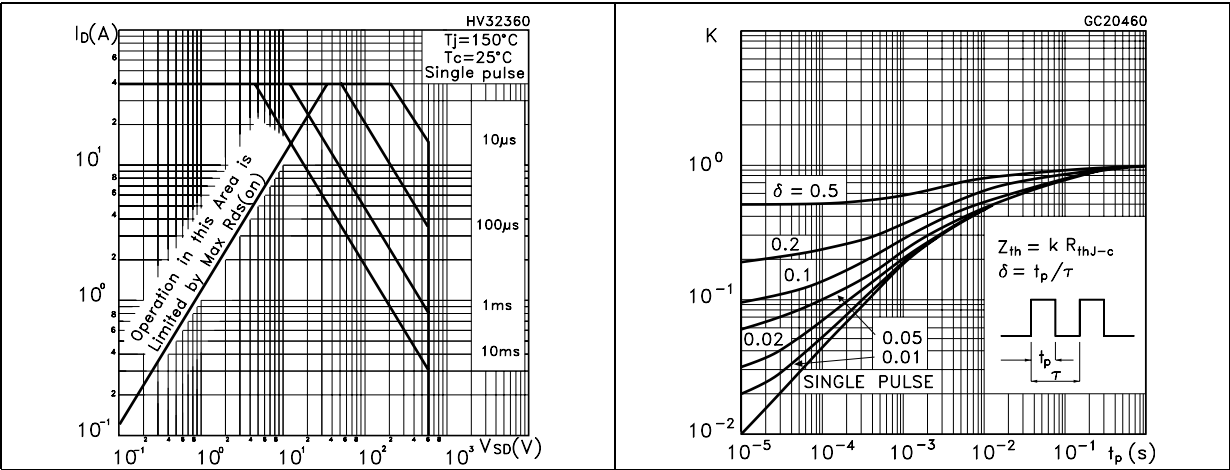


Figure 8. Output characteristics

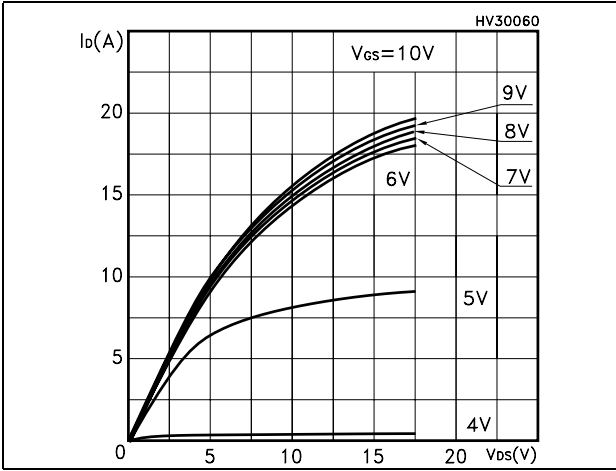


Figure 9. Transfer characteristics

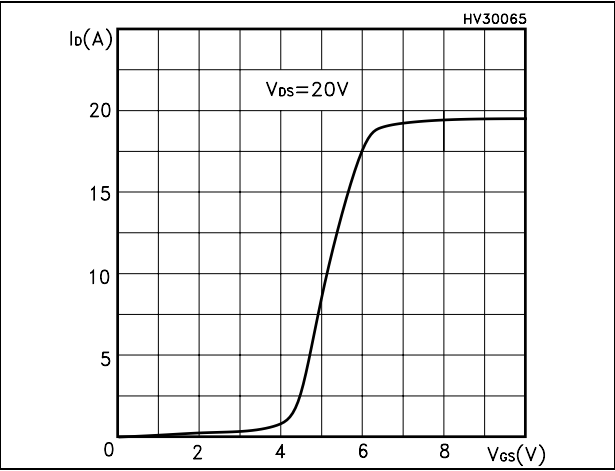


Figure 10. Transconductance

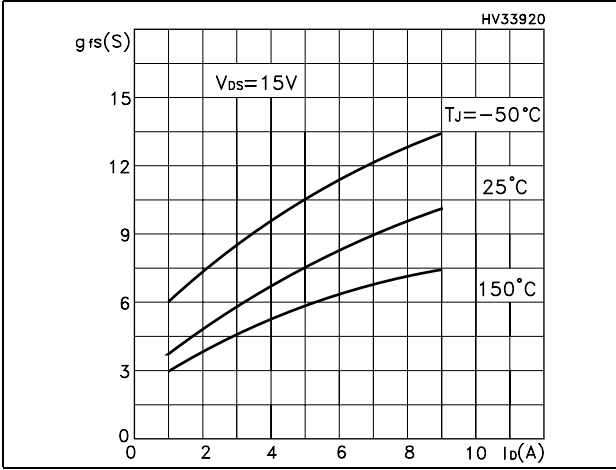


Figure 11. Static drain-source on resistance

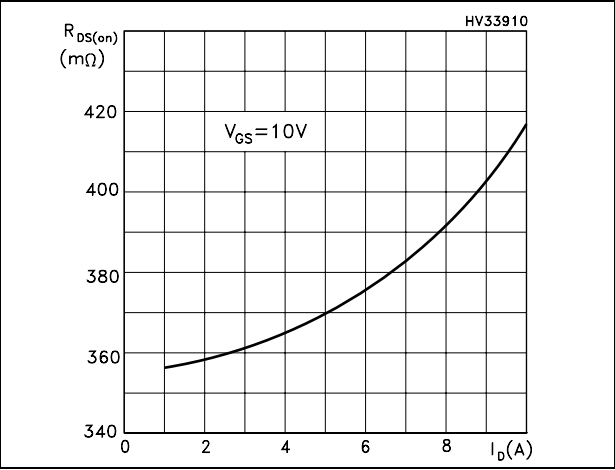


Figure 12. Gate charge vs gate-source voltage Figure 13. Capacitance variations

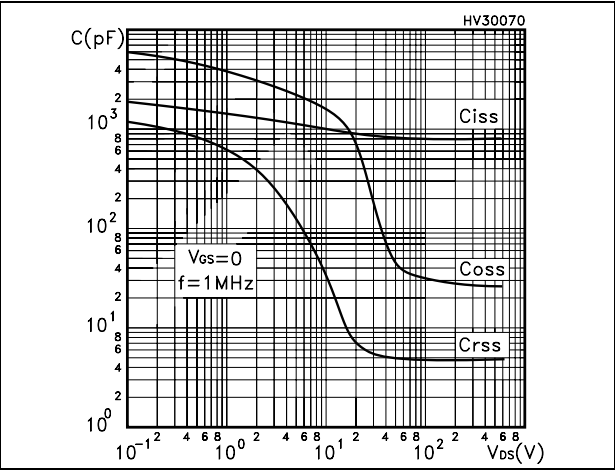
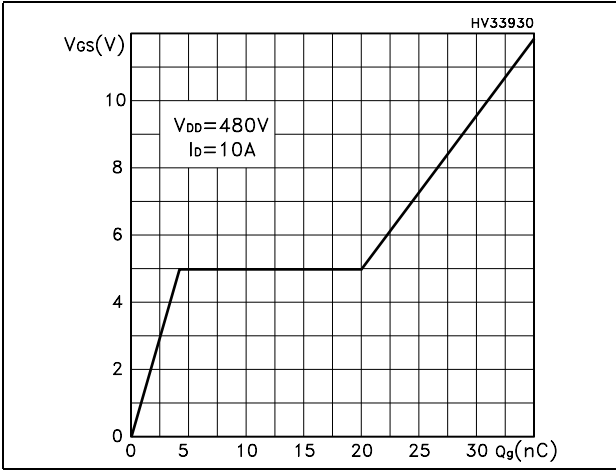


Figure 14. Normalized gate threshold voltage vs temperature

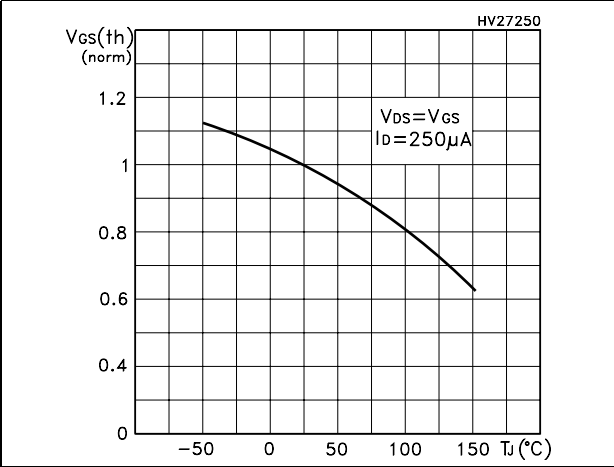


Figure 15. Normalized on resistance vs temperature

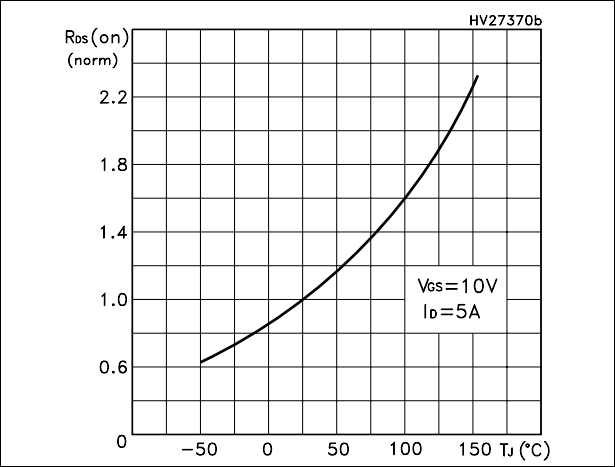


Figure 16. Source-drain diode forward characteristics

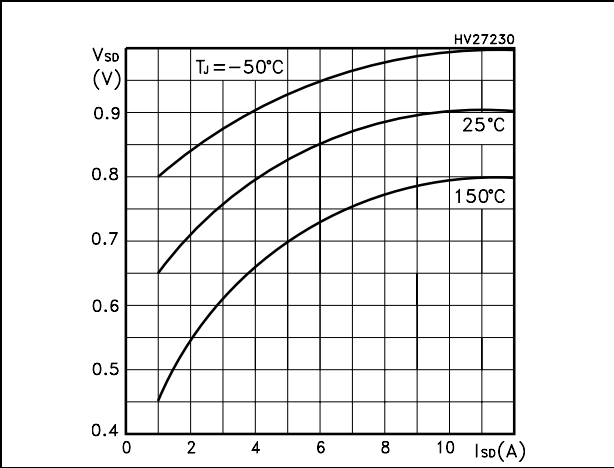
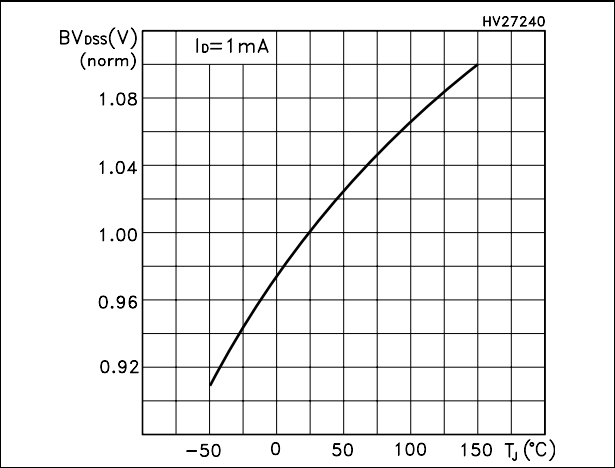


Figure 17. Normalized B_{VDSS} vs temperature



3 Test circuits

Figure 18. Switching times test circuit for resistive load

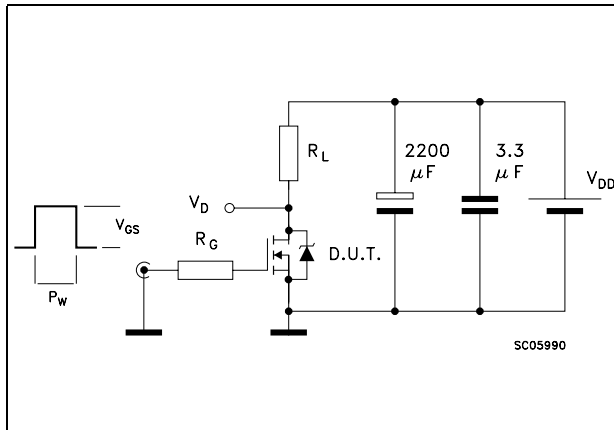


Figure 19. Gate charge test circuit

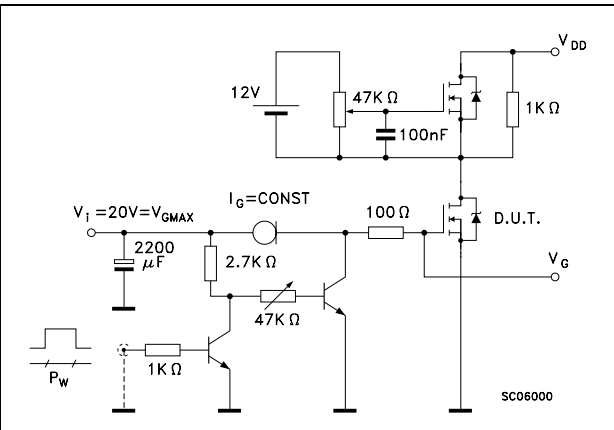


Figure 20. Test circuit for inductive load switching and diode recovery times

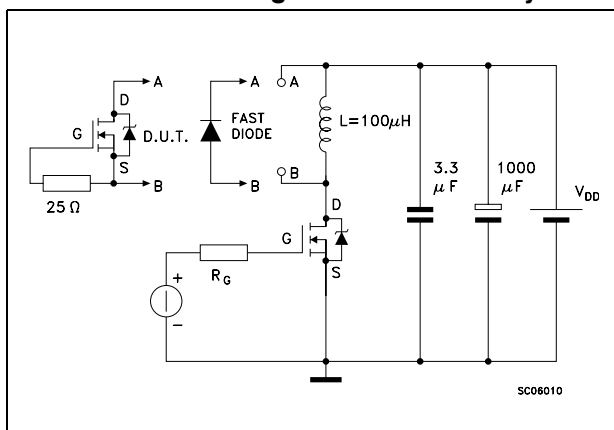


Figure 21. Unclamped inductive load test circuit

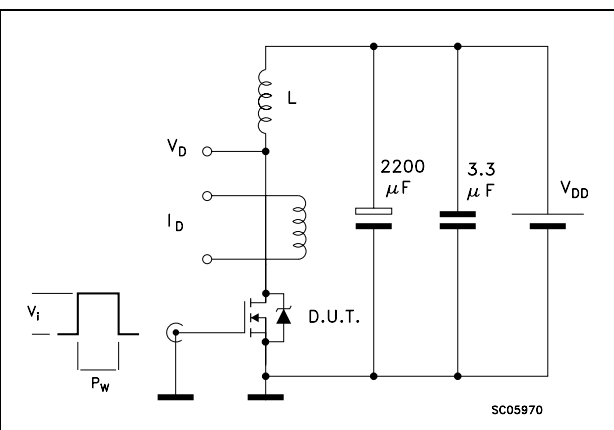


Figure 22. Unclamped inductive waveform

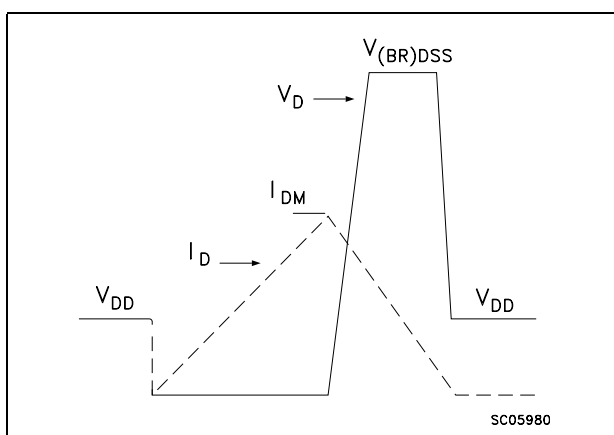
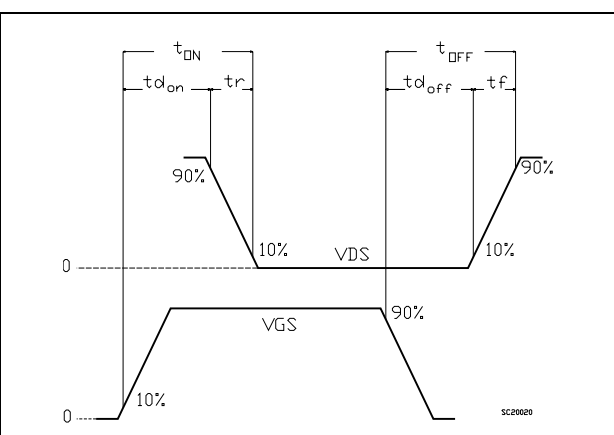


Figure 23. Switching time waveform

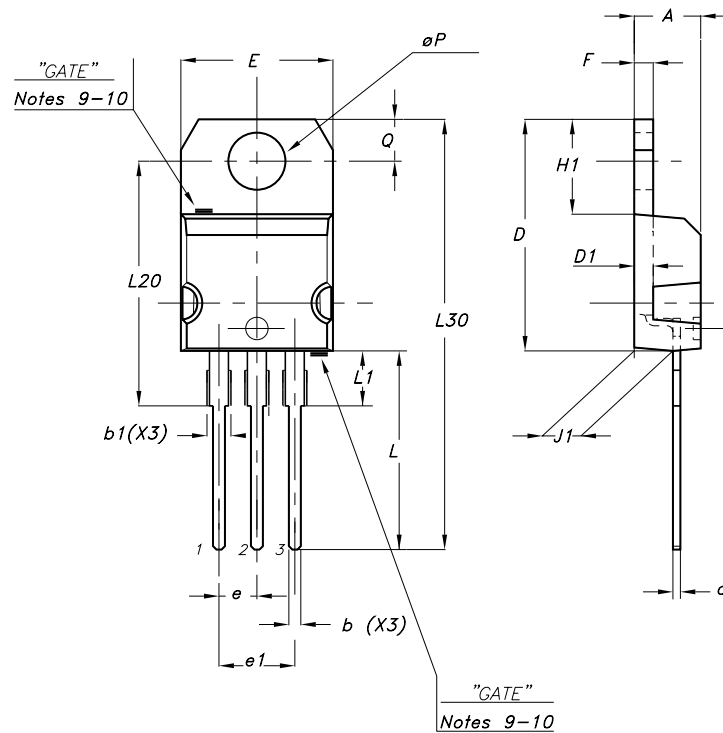


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

TO-220 mechanical data

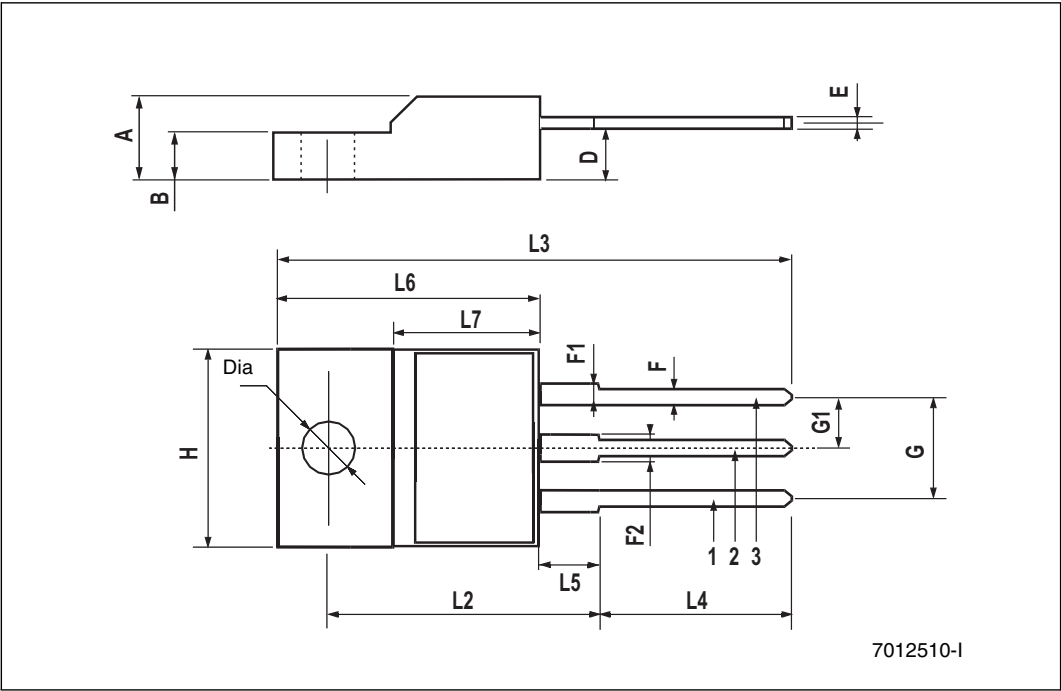
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



0015988_Rev_R

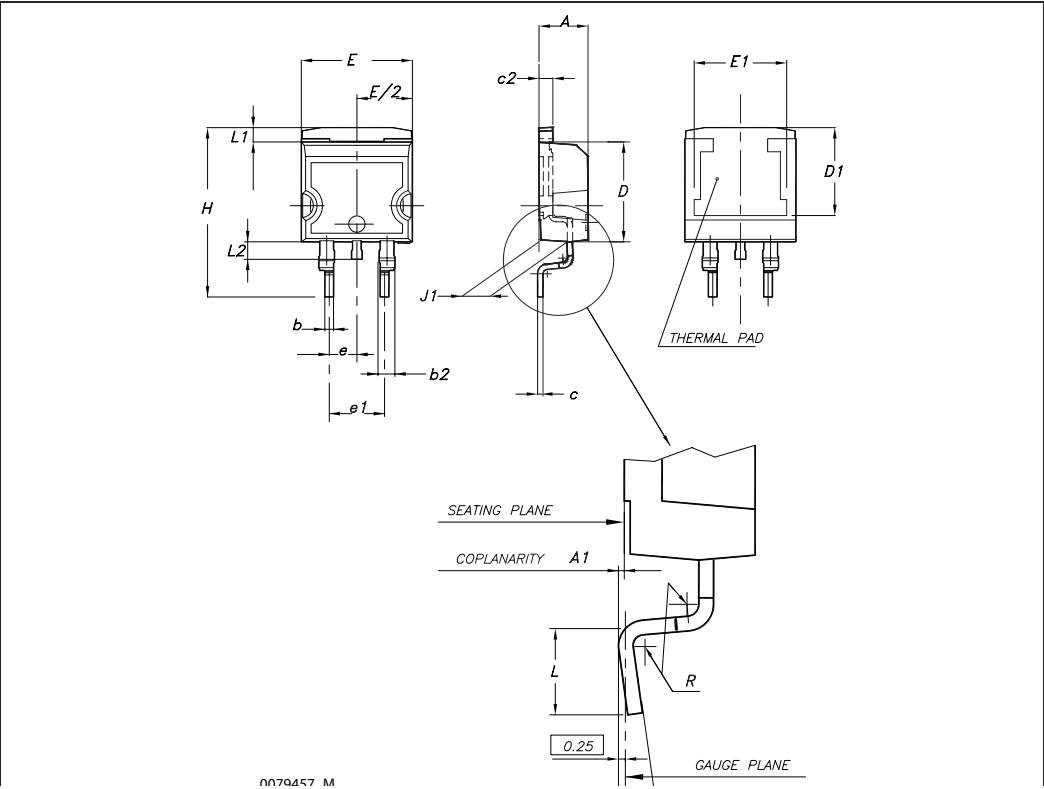
TO-220FP mechanical data

Dim.	mm.			inch		
	Min.	Typ	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.70	0.017		0.027
F	0.75		1.00	0.030		0.039
F1	1.15		1.50	0.045		0.067
F2	1.15		1.50	0.045		0.067
G	4.95		5.20	0.195		0.204
G1	2.40		2.70	0.094		0.106
H	10		10.40	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.80		10.60	0.385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.90		16.40	0.626		0.645
L7	9		9.30	0.354		0.366
Dia	3		3.2	0.118		0.126



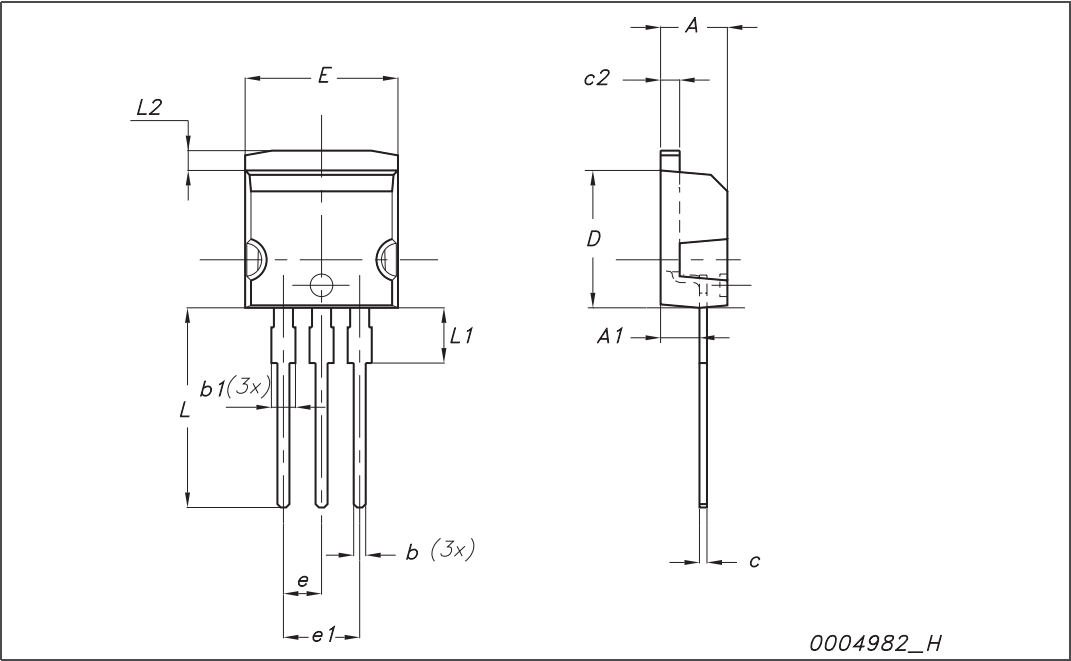
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



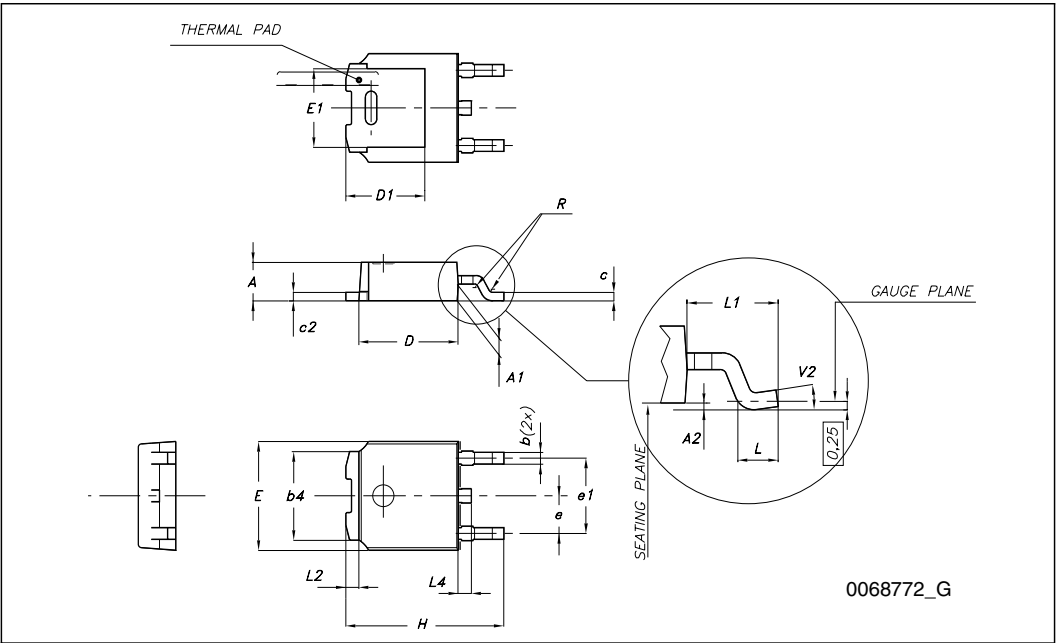
I²PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



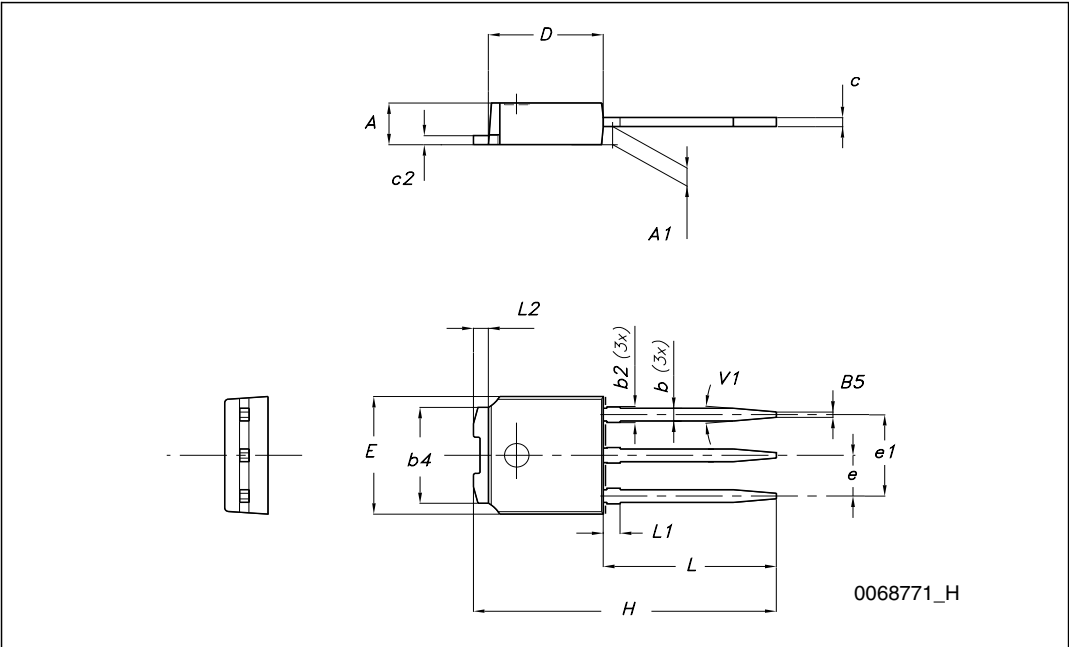
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



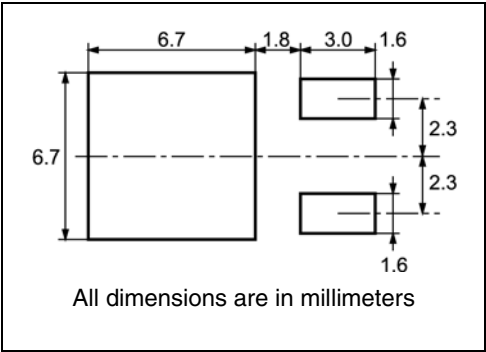
TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	

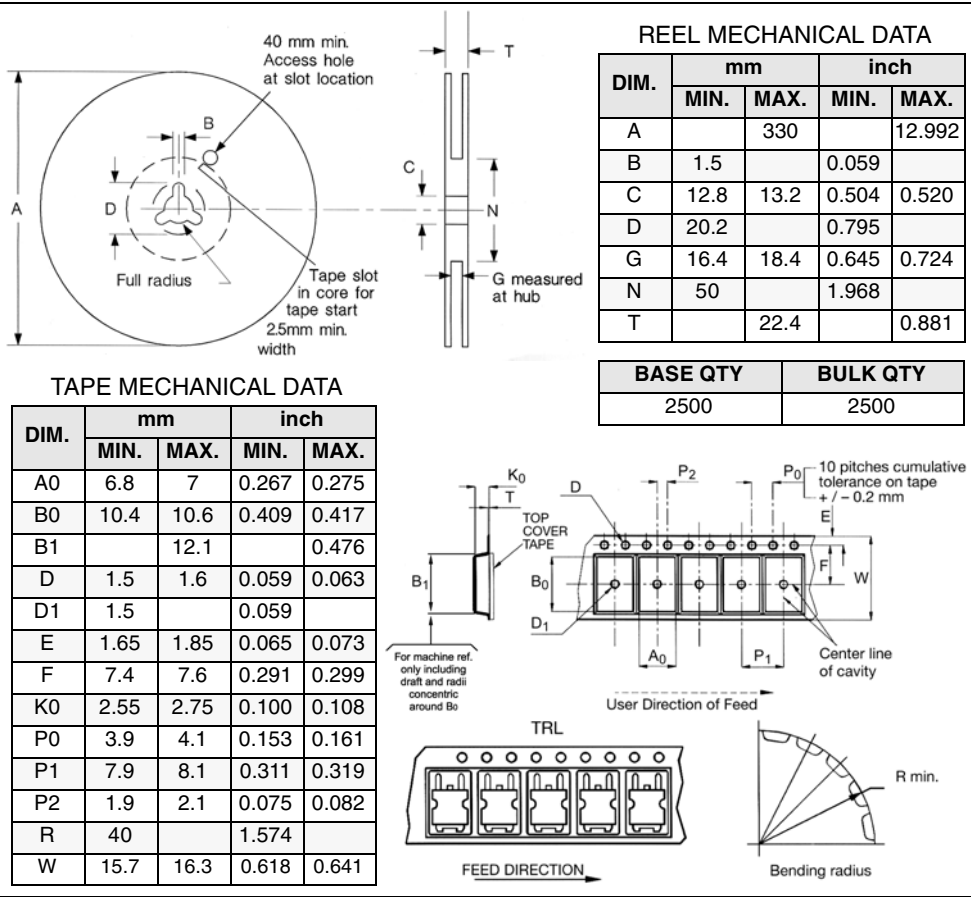


5 Packaging mechanical data

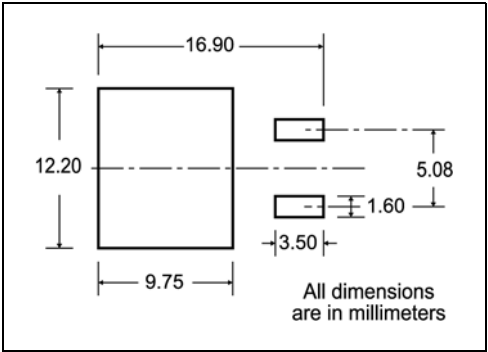
DPAK FOOTPRINT



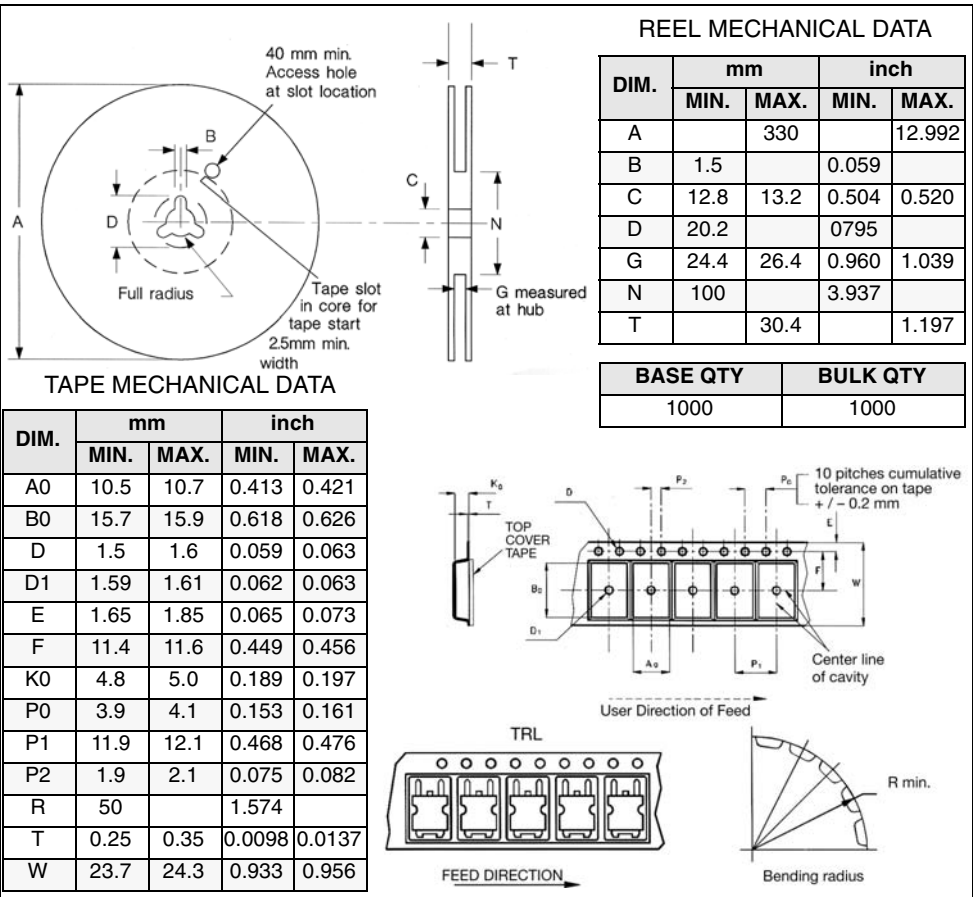
TAPE AND REEL SHIPMENT



D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
03-Aug-2006	1	First release
14-Nov-2006	2	Complete version
02-Oct-2007	3	Figure 8.: Output characteristics has been updated. Added new package (I ² PAK)
03-Mar-2008	4	Added new package D ² PAK
03-Mar-2009	5	Figure 2 , Figure 4 and Figure 6 corrected.

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